

# BAS40WS

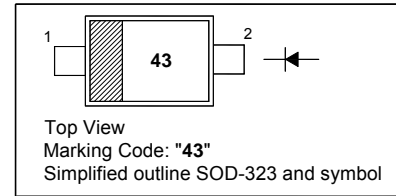
## SURFACE MOUNT SCHOTTKY BARRIER DIODE

### Features

- Low forward voltage
- Fast switching

### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

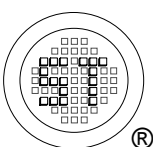


### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	40	V
DC Blocking Voltage	$V_R$	40	V
Forward Continuous Current	$I_F$	200	mA
Peak Forward Surge Current (at $t_p = 8.3\text{ ms}$ )	$I_{FSM}$	600	mA
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{Stg}$	- 55 to + 150	$^\circ\text{C}$

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 1\text{ mA}$ at $I_F = 40\text{ mA}$	$V_F$ $V_F$	- -	0.38 1	V V
Reverse Current at $V_R = 30\text{ V}$	$I_R$	-	200	nA
Reverse Breakdown Voltage at $I_R = 10\text{ }\mu\text{A}$	$V_{(BR)R}$	40	-	V
Reverse Recovery Time at $I_F = I_R = 10\text{ mA}$ to $I_R = 1\text{ mA}$ , $R_L = 100\text{ }\Omega$	$t_{rr}$	-	5	ns
Capacitance at $V_R = 0\text{ V}$ , $f = 1\text{ MHz}$	$C_j$	-	5	pF



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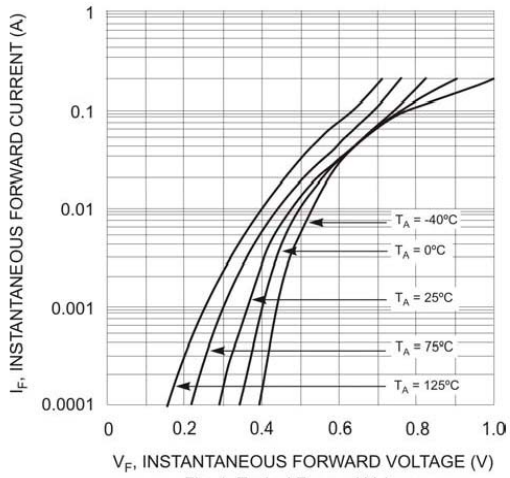


Fig. 1 Typical Forward Voltage

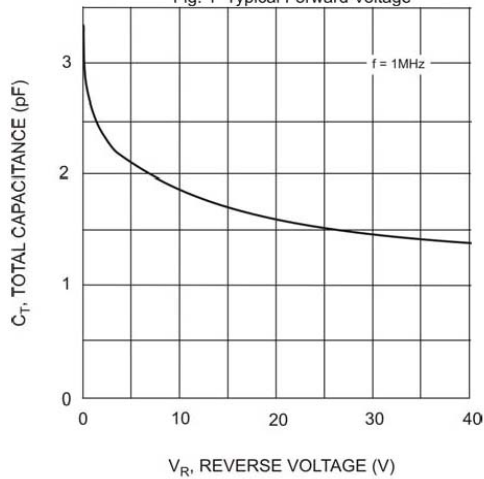


Fig. 3 Typical Capacitance

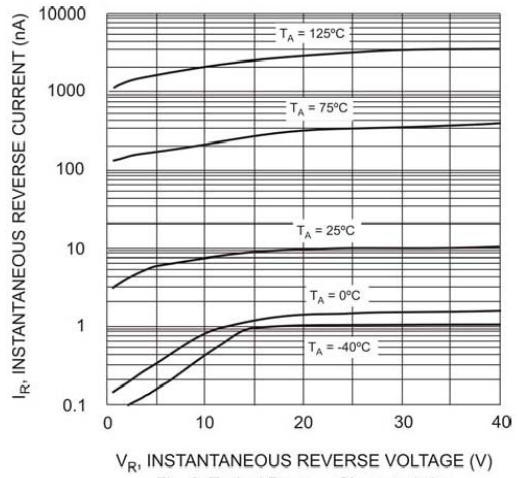
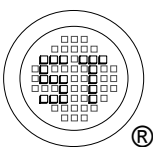


Fig. 2 Typical Reverse Characteristics



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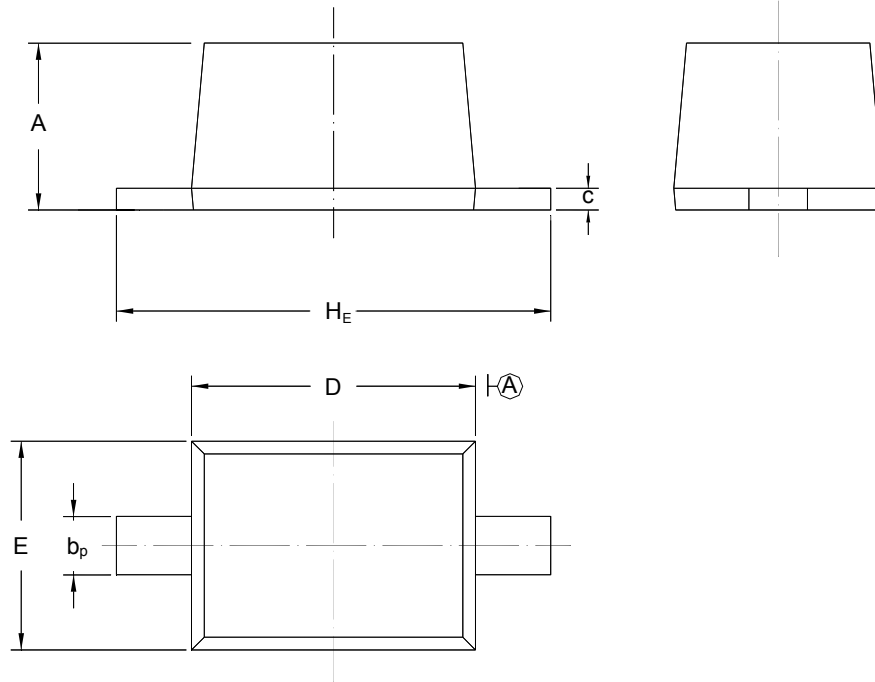
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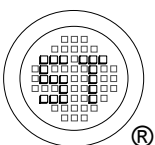
## PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



UNIT	A	b <sub>p</sub>	C	D	E	H <sub>E</sub>
mm	1.10 0.80	0.40 0.25	0.15 0.10	1.80 1.60	1.35 1.15	2.80 2.30



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